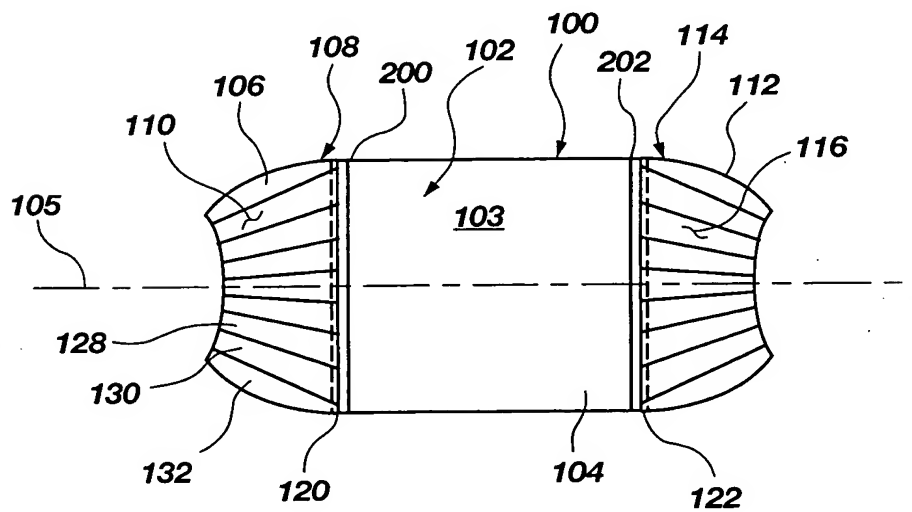
**FIG. 1**

FIG. 2

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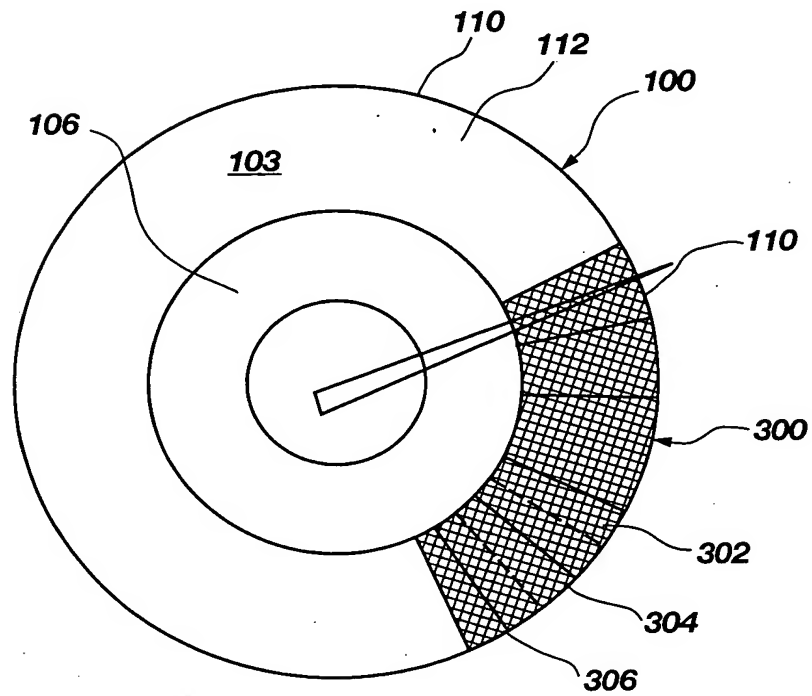


FIG. 3

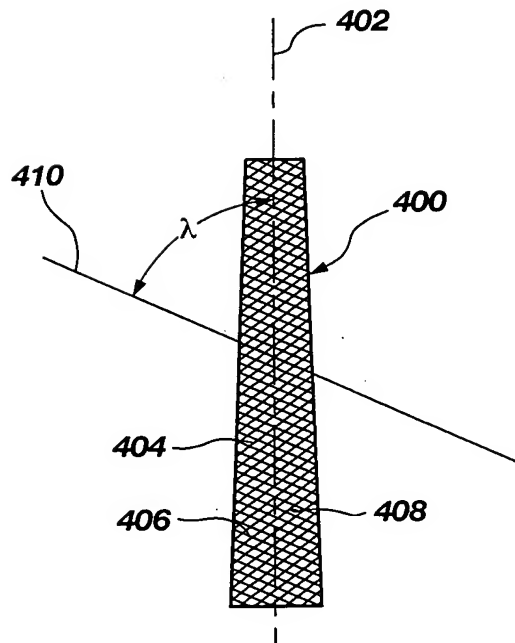


FIG. 4

A cross-sectional view of a semiconductor device. A central layer, labeled 300, is positioned on a substrate 102. The substrate 102 is shown with diagonal hatching. Above the substrate 102, there is a layer 110, also with diagonal hatching. On top of layer 110, there is a layer 302. A central feature, labeled 304, is formed in layer 302. This feature 304 is surrounded by a layer 306. The top surface of feature 304 is labeled 600. The side walls of feature 304 are labeled 602 and 604. The top surface of layer 302 is labeled 606. The side walls of layer 302 are labeled 610 and 612. The bottom surface of layer 302 is labeled 608.

A cross-sectional view of a semiconductor device 300. The device consists of a substrate 102 with a top surface 103 and a bottom surface 110. A layer 702 is formed on the top surface 103. A layer 704 is formed on the top surface 103, and a layer 706 is formed on the top surface 103. A layer 302 is formed on the top surface 103, and a layer 304 is formed on the top surface 103. A layer 306 is formed on the top surface 103.

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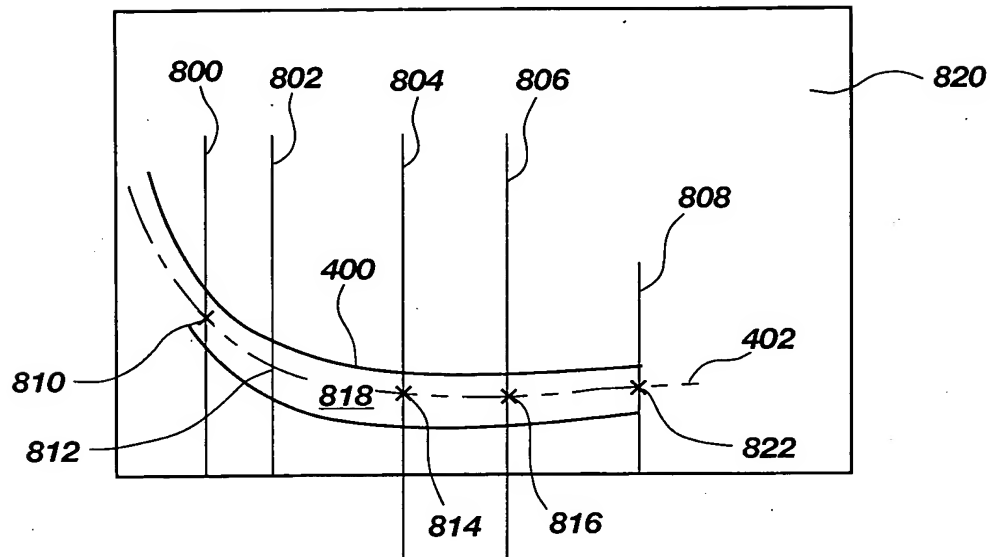


FIG. 8

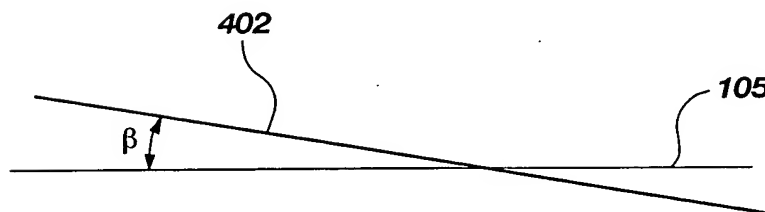


FIG. 9

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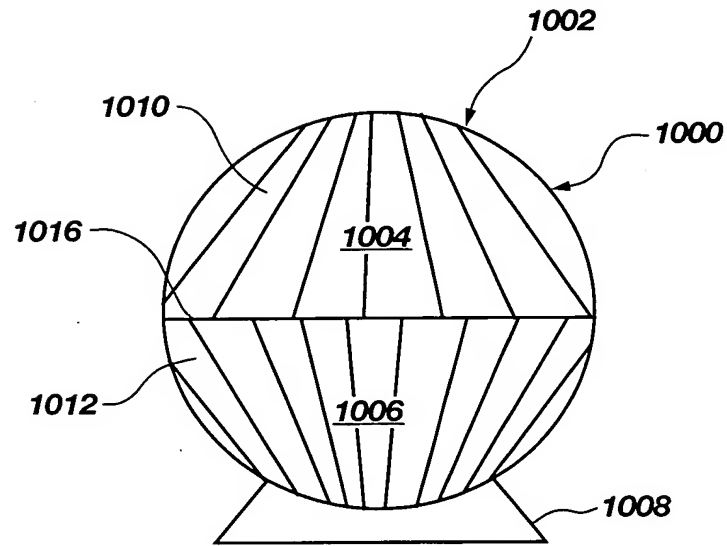


FIG. 10